

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE6802 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge .This device is suitable for use as a load switch or in PWM applications.

General Features

• $V_{DS} = 30V, I_D = 3.5A$

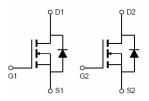
 $R_{DS(ON)} < 70 \text{m}\Omega$ @ V_{GS} =4.5V

 $R_{DS(ON)}$ <45m Ω @ V_{GS} =10V

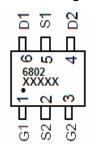
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

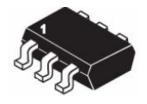
- Battery protection
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT23-6L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
6802	NCE6802	SOT-23-6L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	3.5	Α
Drain Current-Pulsed (Note 1)	I _{DM}	20	Α
Maximum Power Dissipation	P _D	1.2	W
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	104	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V



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NCE6802

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μΑ	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =250μA	1.2	1.5	2.2	V	
Drain-Source On-State Resistance	D.	V _{GS} =10V, I _D =3.5A	-	36	45	mΩ	
Dialii-Source Oil-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =2A	-	59	70	mΩ	
Forward Transconductance	g FS	V _{DS} =5V,I _D =3.5A	-	12	-	S	
Dynamic Characteristics (Note4)			•				
Input Capacitance	C _{iss}	\/ -15\/\/ -0\/	-	170	-	PF	
Output Capacitance	Coss	V_{DS} =15V, V_{GS} =0V, F=1.0MHz	-	35	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.0WHZ	-	23	-	PF	
Switching Characteristics (Note 4)			•				
Turn-on Delay Time	t _{d(on)}		-	4.5	-	nS	
Turn-on Rise Time	t _r	V_{DS} =15V, R_L =4.2 Ω	-	1.5	-	nS	
Turn-Off Delay Time	$t_{\sf d(off)}$	V_{GS} =10 V , R_{GEN} =3 Ω	-	18.5	-	nS	
Turn-Off Fall Time	t _f		-	15.5	-	nS	
Total Gate Charge	Q_g	\/ -45\/ -2.50	-	4.0	-	nC	
Gate-Source Charge	Q_{gs}	V _{DS} =15V,I _D =3.5A,	-	0.75	-	nC	
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	0.65	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =3.5A	-	8.0	1.2	V	
Diode Forward Current (Note 2)	I _S		-	-	3.5	Α	

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

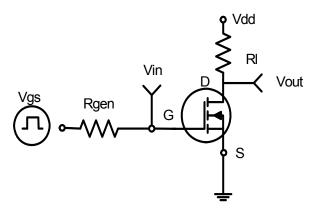
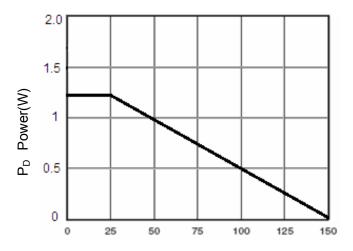


Figure 1:Switching Test Circuit



 T_J -Junction Temperature(°C) Figure 3 Power Dissipation

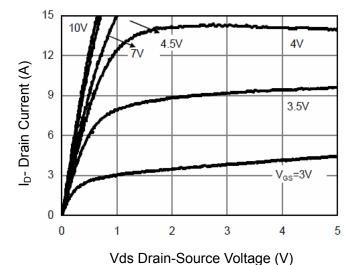


Figure 5 Output Characteristics

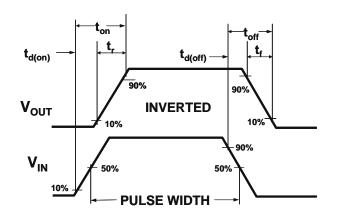


Figure 2:Switching Waveforms

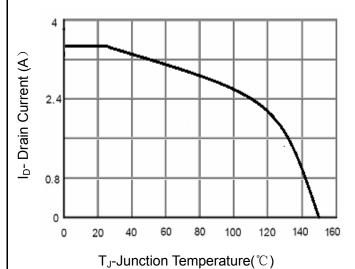


Figure 4 Drain Current

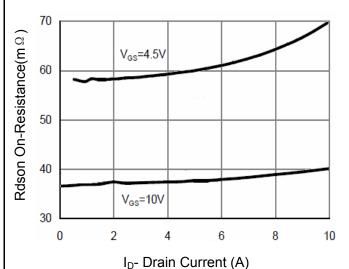
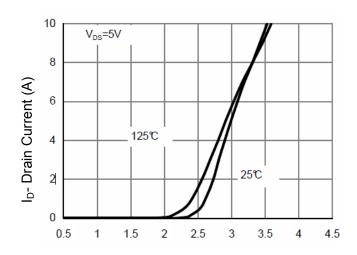
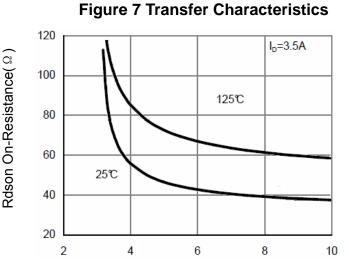


Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

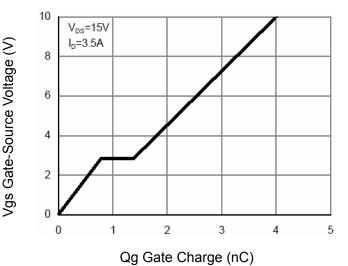


Figure 11 Gate Charge

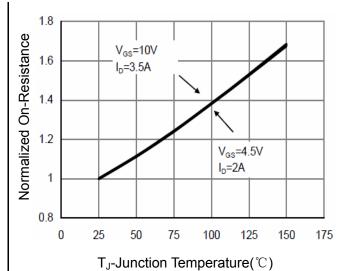


Figure 8 Drain-Source On-Resistance

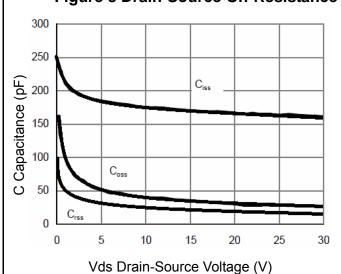


Figure 10 Capacitance vs Vds

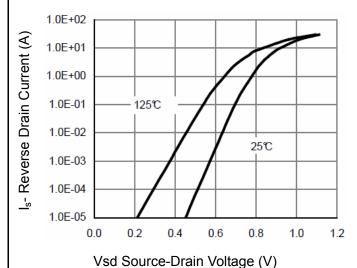


Figure 12 Source- Drain Diode Forward



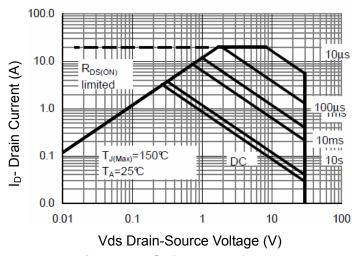


Figure 13 Safe Operation Area

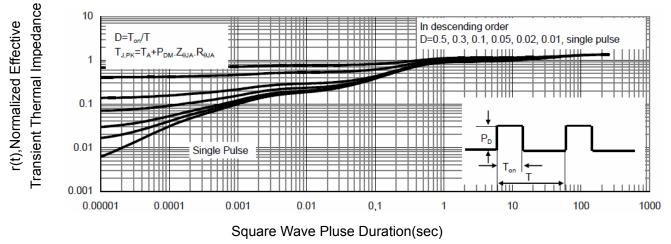
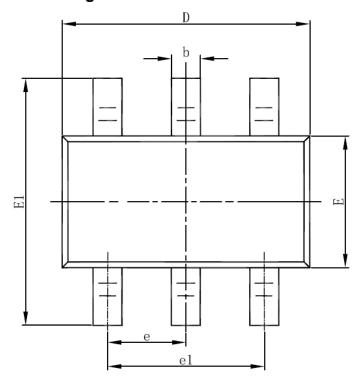
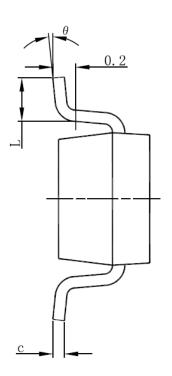


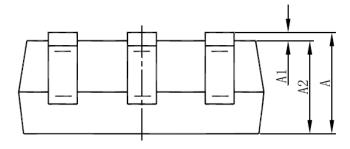
Figure 14 Normalized Maximum Transient Thermal Impedance



SOT23-6L Package Information







Ck a l	Dimensions Ir	n Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950	(BSC)	0.037	(BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	



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